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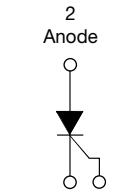
Thyristor High Voltage, Surface Mountable Phase Control SCR, 16 A

TO-263AB (D^2PAK)



FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Designed and qualified according JEDEC-JESD47
- Compliant to RoHS Directive 2002/95/EC
- Halogen-free according to IEC 61249-2-21 definition

Pb

e3

RoHS COMPLIANT

HALOGEN FREE

APPLICATIONS

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-16TTS..SPbF high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

PRODUCT SUMMARY	
Package	TO-263AB (D^2PAK)
Diode variation	Single SCR
$I_{T(AV)}$	10 A
V_{DRM}/V_{RRM}	800 V, 1200 V
V_{TM}	1.4 V
I_{GT}	60 mA
T_J	- 40 °C to 125 °C

OUTPUT CURRENT IN TYPICAL APPLICATIONS			
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 µm) copper	2.5	3.5	A
Aluminum IMS, R_{thCA} = 15 °C/W	6.3	9.5	
Aluminum IMS with heatsink, R_{thCA} = 5 °C/W	14.0	18.5	

Note

- T_A = 55 °C, T_J = 125 °C, footprint 300 mm^2

MAJOR RATINGS AND CHARACTERISTICS			
SYMBOL	CHARACTERISTICS	VALUES	UNITS
$I_{T(AV)}$	Sinusoidal waveform	10	A
I_{RMS}		16	
V_{RRM}/V_{DRM}		800/1200	V
I_{TSM}		200	A
V_T	10 A, T_J = 25 °C	1.4	V
dV/dt		500	V/µs
dI/dt		150	A/µs
T_J		- 40 to 125	°C

VOLTAGE RATINGS			
PART NUMBER	V_{RRM}, MAXIMUM PEAK REVERSE VOLTAGE V	V_{DRM}, MAXIMUM PEAK DIRECT VOLTAGE V	I_{RRM}/I_{DRM} AT 125 °C mA
VS-16TTS08SPbF	800	800	10
VS-16TTS12SPbF	1200	1200	

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES TYP.	VALUES MAX.	UNITS
Maximum average on-state current	$I_{T(AV)}$	T_C = 98 °C, 180° conduction, half sine wave	10		A
Maximum RMS on-state current	I_{RMS}		16		A
Maximum peak, one-cycle, non-repetitive surge current	I_{TSM}	10 ms sine pulse, rated V_{RRM} applied	170		A
		10 ms sine pulse, no voltage reapplied	200		A
Maximum I^2t for fusing	I^2t	10 ms sine pulse, rated V_{RRM} applied	144		A^2s
		10 ms sine pulse, no voltage reapplied	200		A^2s
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 ms to 10 ms, no voltage reapplied	2000		$A^2\sqrt{s}$
Maximum on-state voltage drop	V_{TM}	10 A, T_J = 25 °C	1.4		V
On-state slope resistance	r_t	T_J = 125 °C	24.0		mΩ
Threshold voltage	$V_{T(TO)}$	T_J = 125 °C	1.1		V
Maximum reverse and direct leakage current	I_{RM}/I_{DM}	T_J = 25 °C, V_R = Rated V_{RRM}/V_{DRM}	0.5		mA
		T_J = 125 °C, V_R = Rated V_{RRM}/V_{DRM}	10		mA
Holding current	I_H	Anode supply = 6 V, resistive load, initial I_T = 1 A	-	100	mA
Maximum latching current	I_L	Anode supply = 6 V, resistive load	200		mA
Maximum rate of rise of off-state voltage	dV/dt		500		V/µs
Maximum rate of rise of turned-on current	dI/dt		150		A/µs

TRIGGERING

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P_{GM}		8.0	W
Maximum average gate power	$P_{G(AV)}$		2.0	W
Maximum peak positive gate current	+ I_{GM}		1.5	A
Maximum peak negative gate voltage	- V_{GM}		10	V
Maximum required DC gate current to trigger	I_{GT}	Anode supply = 6 V, resistive load, T_J = - 10 °C	90	mA
		Anode supply = 6 V, resistive load, T_J = 25 °C	60	mA
		Anode supply = 6 V, resistive load, T_J = 125 °C	35	mA
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, T_J = - 10 °C	3.0	V
		Anode supply = 6 V, resistive load, T_J = 25 °C	2.0	V
		Anode supply = 6 V, resistive load, T_J = 125 °C	1.0	V
Maximum DC gate voltage not to trigger	V_{GD}	T_J = 125 °C, V_{DRM} = Rated value	0.25	
Maximum DC gate current not to trigger	I_{GD}		2.0	mA

SWITCHING

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t_{gt}	T_J = 25 °C	0.9	µs
Typical reverse recovery time	t_{rr}	T_J = 125 °C	4	µs
Typical turn-off time	t_q		110	µs

THERMAL - MECHANICAL SPECIFICATIONS				
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**VALUES**	**UNITS**
Maximum junction and storage temperature range	T_J, T_{Stg}		- 40 to 125	°C
Soldering temperature	T_S	For 10 s (1.6 mm from case)	240	
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	1.3	°C/W
Typical thermal resistance, junction to ambient	R_{thJA}	PCB mount (1)	40	
Approximate weight			2	g
			0.07	oz.
Marking device		Case style D^2PAK (SMD-220)	16TTS08S	
			16TTS12S	

Note

(1) When mounted on 1" square (650 mm^2) PCB of FR-4 or G-10 material 4 oz. (140 µm) copper 40 °C/W.
For recommended footprint and soldering techniques refer to application note #AN-994.

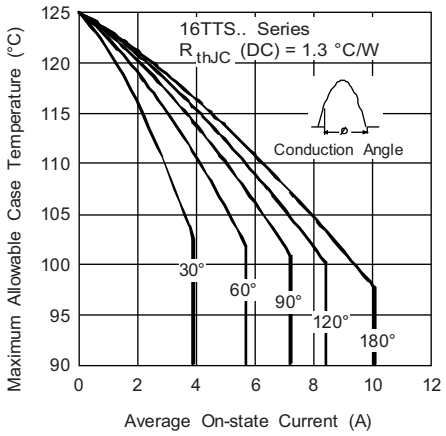


Fig. 1 - Current Rating Characteristics

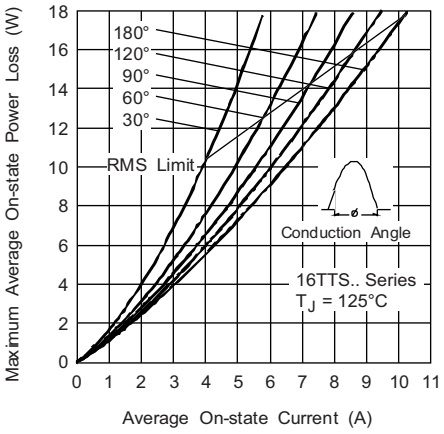


Fig. 3 - On-State Power Loss Characteristics

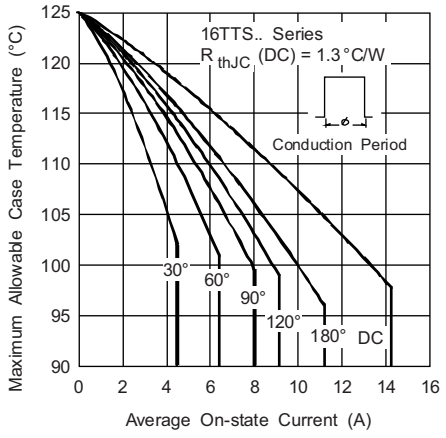


Fig. 2 - Current Rating Characteristics

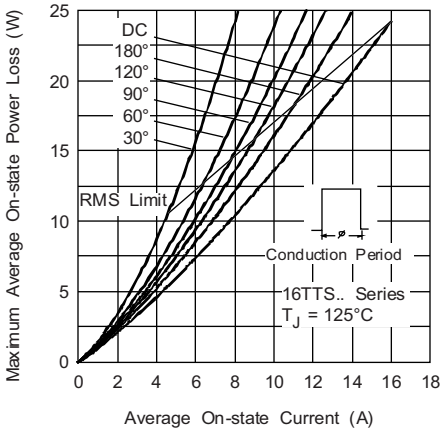


Fig. 4 - On-State Power Loss Characteristics

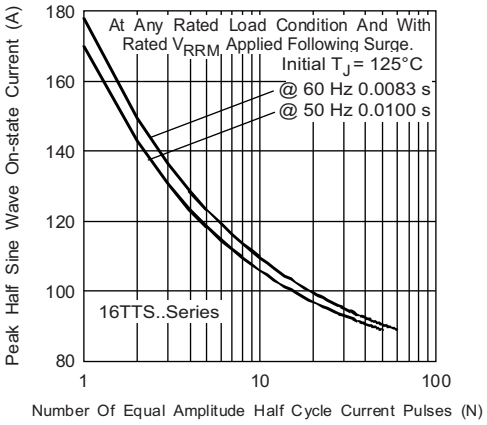


Fig. 5 - Maximum Non-Repetitive Surge Current

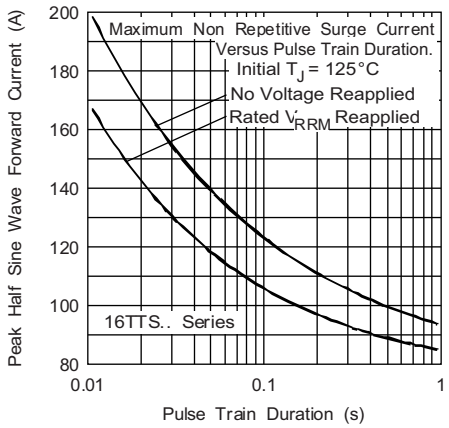


Fig. 6 - Maximum Non-Repetitive Surge Current

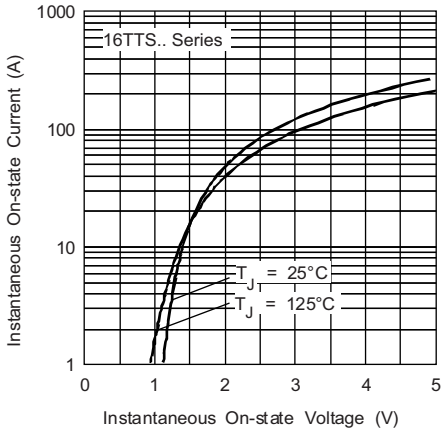


Fig. 7 - On-State Voltage Drop Characteristics

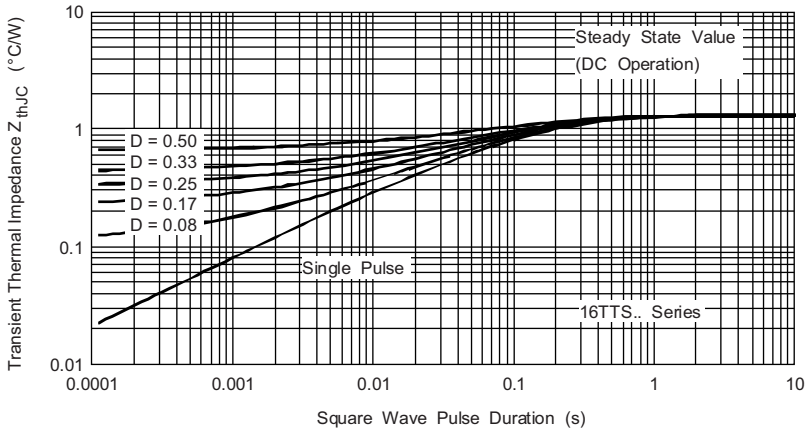


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

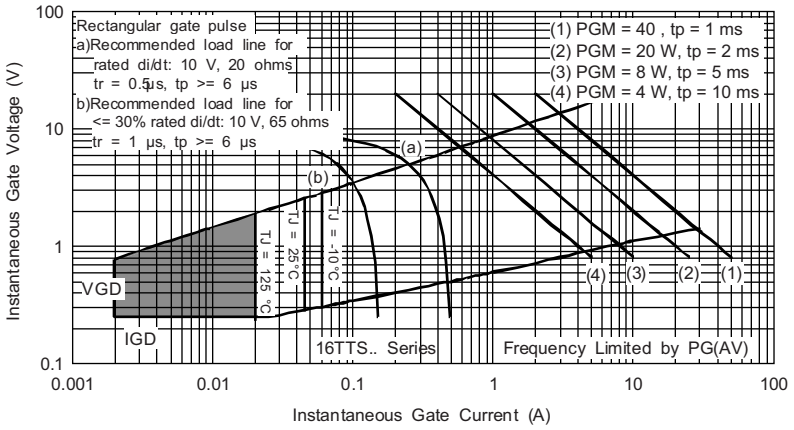


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code

VS-	16	T	T	S	12	S	TRL	PbF
1	2	3	4	5	6	7	8	9

1 - Vishay Semiconductors product

2 - Current rating

3 - Circuit configuration:
T = Single thyristor

4 - Package:
T = TO-220AC

5 - Type of silicon:
S = Standard recovery rectifier

6 - Voltage rating: Voltage code x 100 = V_{RRM} (08 = 800 V, 12 = 1200 V)

7 - S = D^2PAK version

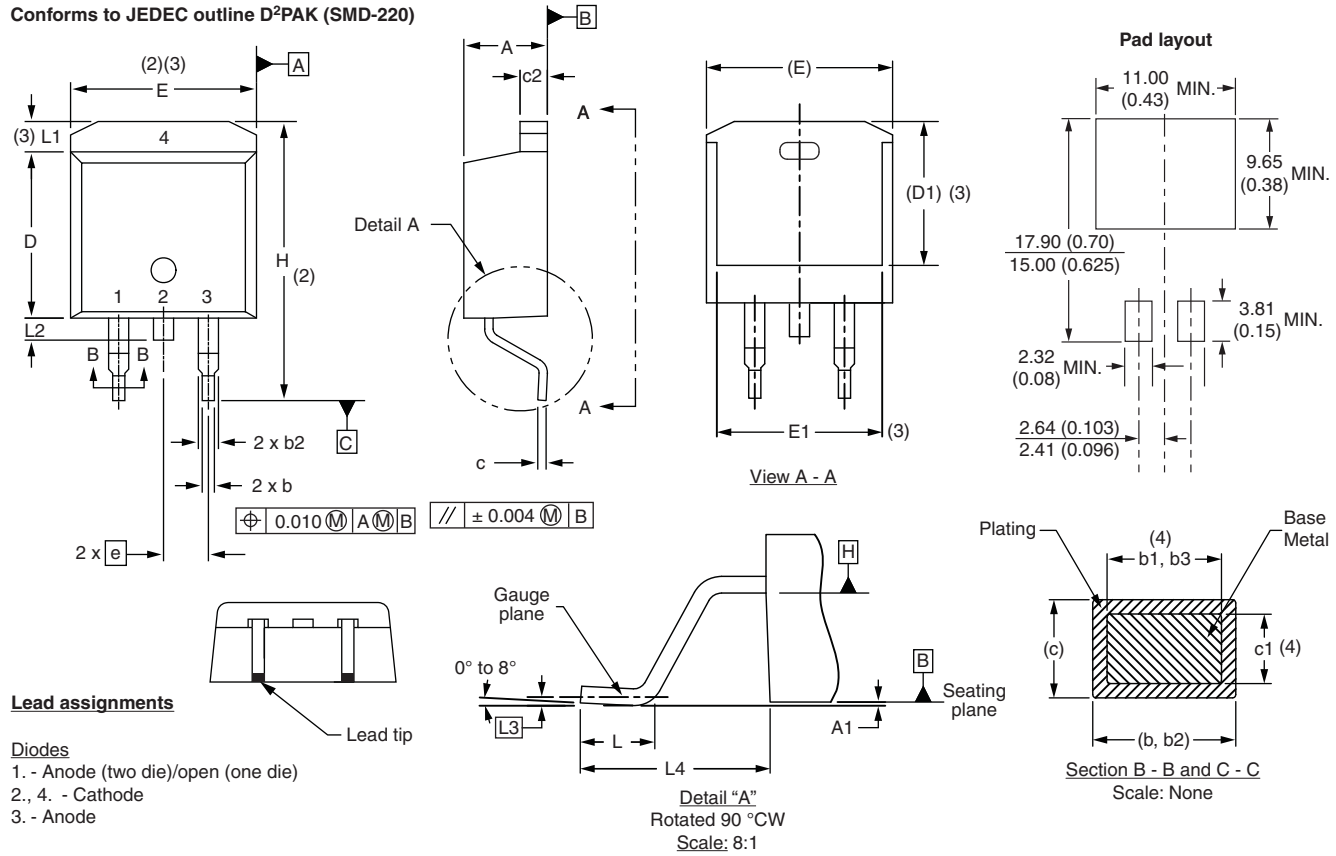
8 - • None = Tube
• TRL = Tape and reel (left oriented)
• TRR = Tape and reel (right oriented)

9 - PbF = Lead (Pb)-free and RoHS compliant

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95046
Part marking information	www.vishay.com/doc?95054
Packaging information	www.vishay.com/doc?95032

D^2PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
c	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
e	2.54 BSC		0.100 BSC		
H	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25 BSC		0.010 BSC		
L4	4.78	5.28	0.188	0.208	

Notes

(1) Dimensioning and tolerancing per ASME Y14.5 M-1994
(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
(3) Thermal pad contour optional within dimension E, L1, D1 and E1
(4) Dimension b1 and c1 apply to base metal only
(5) Datum A and B to be determined at datum plane H
(6) Controlling dimension: inch
(7) Outline conforms to JEDEC outline TO-263AB

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